

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max $T_C = +25^\circ C$
-60V	33m Ω @ $V_{GS} = -10V$	-35A
	40m Ω @ $V_{GS} = -4.5V$	-32A

Description

This MOSFET has been designed to meet the stringent requirements of Automotive applications.

Applications

It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DCDC Converters

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

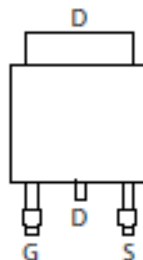
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.33 grams (Approximate)

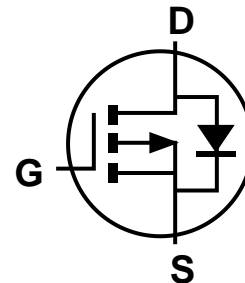


Top View

TO252 (DPAK)



Pin Out Top View



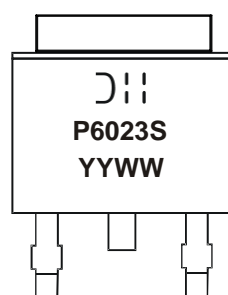
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH6023SK3-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



Diodes logo = Manufacturer's Marking
 P6023S = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 15 = 2015)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _C = +25°C T _C = +100°C	I _D	-35 -27	A
	Steady State	T _A = +25°C T _A = +70°C	I _D	-7.3 -6.1	A
Pulsed Drain Current (380µs pulse, duty cycle = 1%)			I _{DM}	-60	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-2.2	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-35	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	60	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	80	°C/W
Total Power Dissipation (Note 6)		P _D	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	41	°C/W
Thermal Resistance, Junction to Case		R _{θJC}	1.6	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	µA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	33	mΩ	V _{GS} = -10V, I _D = -10A
		—	—	40		V _{GS} = -4.5V, I _D = -8A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2,569	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	179	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	143	—	pF	
Gate Resistance	R _g	—	5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	26.5	—	nC	V _{DS} = -30V, I _D = -5A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	53.1	—	nC	
Gate-Source Charge	Q _{gs}	—	7.1	—	nC	
Gate-Drain Charge	Q _{gd}	—	12.6	—	nC	
Turn-On Delay Time	t _{D(on)}	—	6	—	nS	V _{GS} = -10V, V _{DS} = -30V, R _G = 3Ω, I _D = -5A
Turn-On Rise Time	t _r	—	7.1	—	nS	
Turn-Off Delay Time	t _{D(off)}	—	110	—	nS	
Turn-Off Fall Time	t _f	—	62	—	nS	I _F = -5A, di/dt = 100A/µs
Body Diode Reverse Recovery Time	t _{rr}	—	20	—	nS	
Body Diode Reverse Recovery Charge	Q _{rr}	—	14	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout, see <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

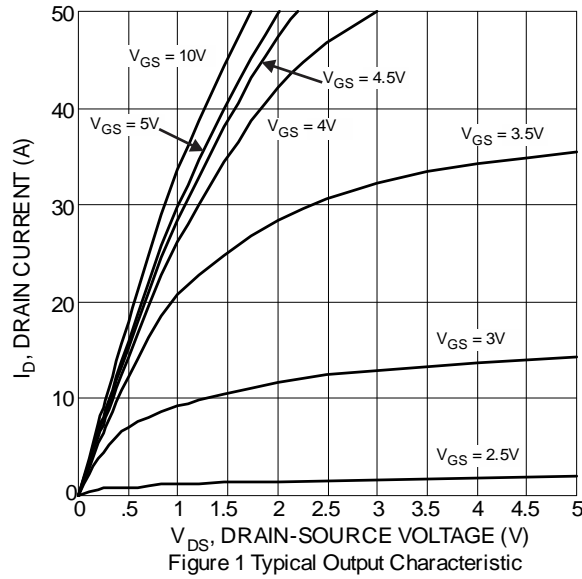


Figure 1 Typical Output Characteristic

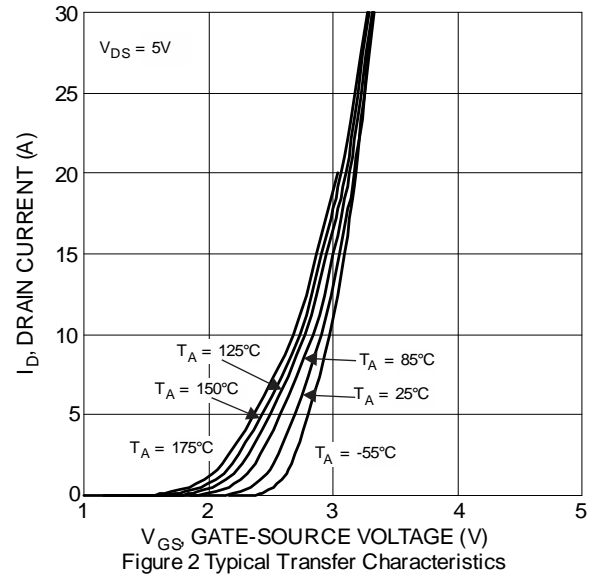


Figure 2 Typical Transfer Characteristics

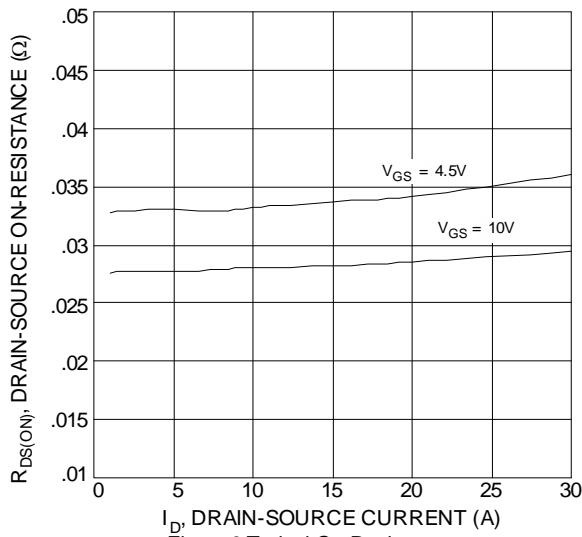


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

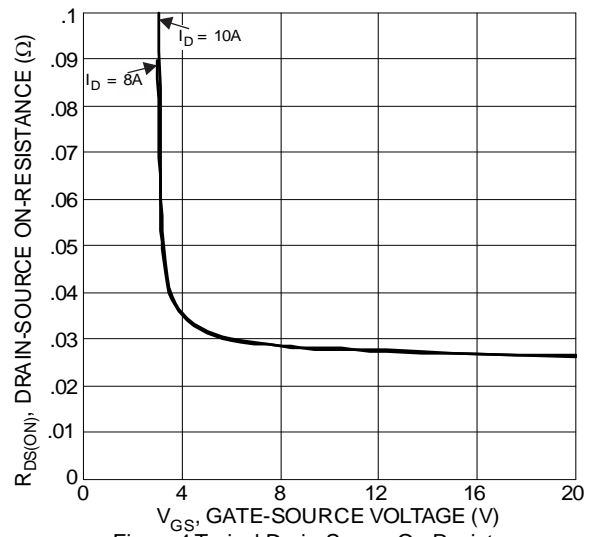


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

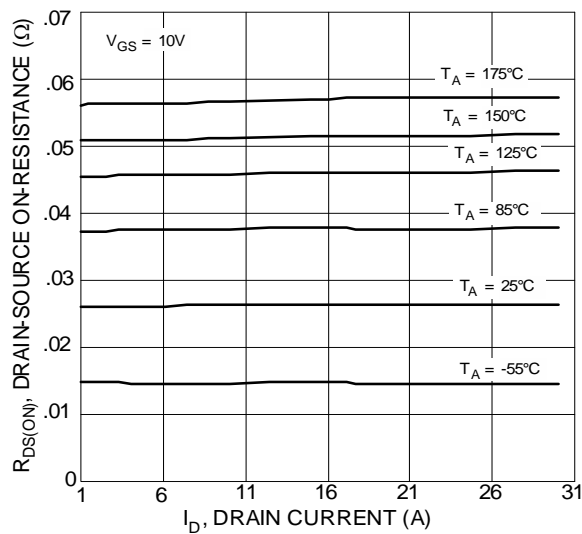


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

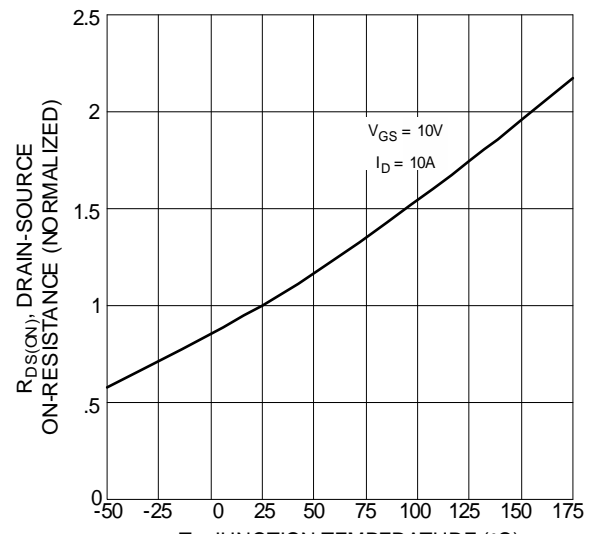
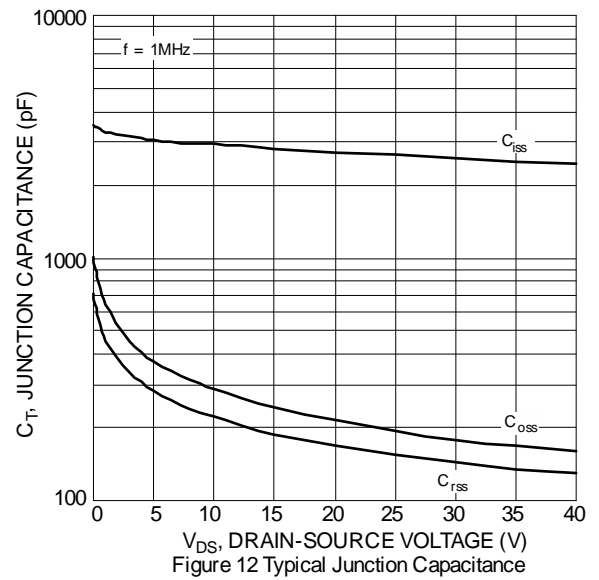
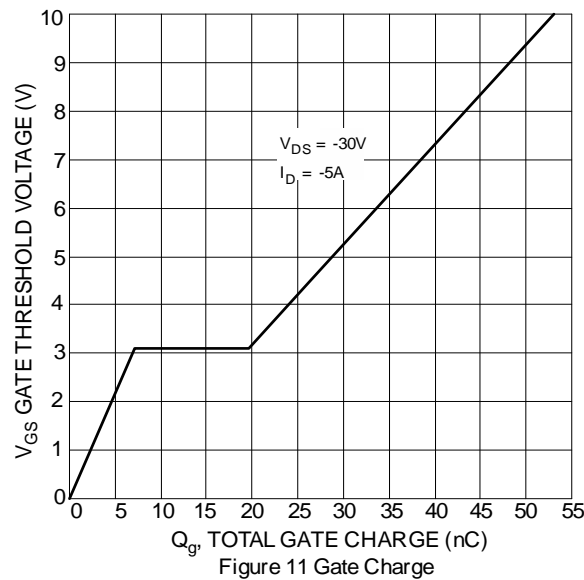
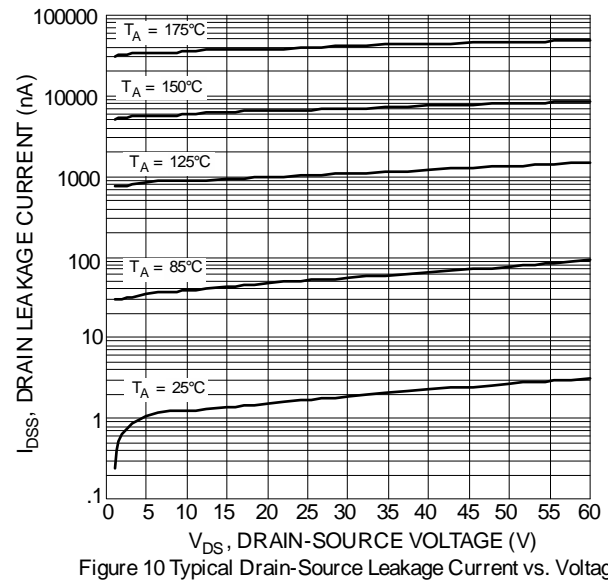
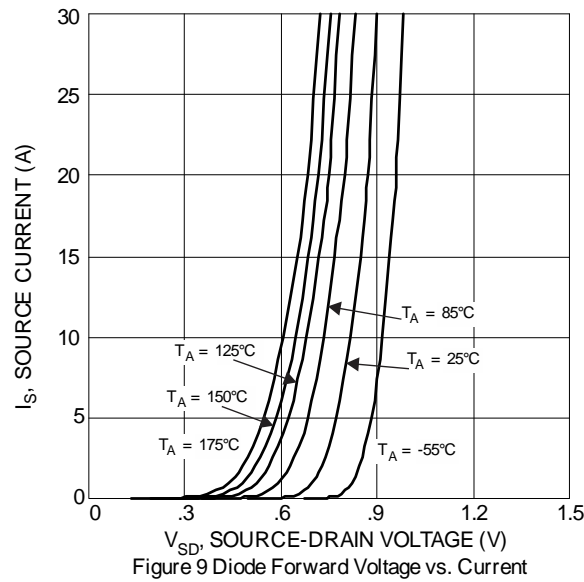
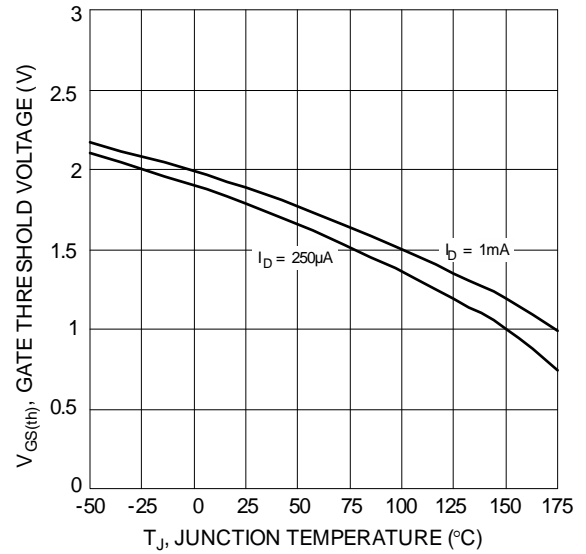
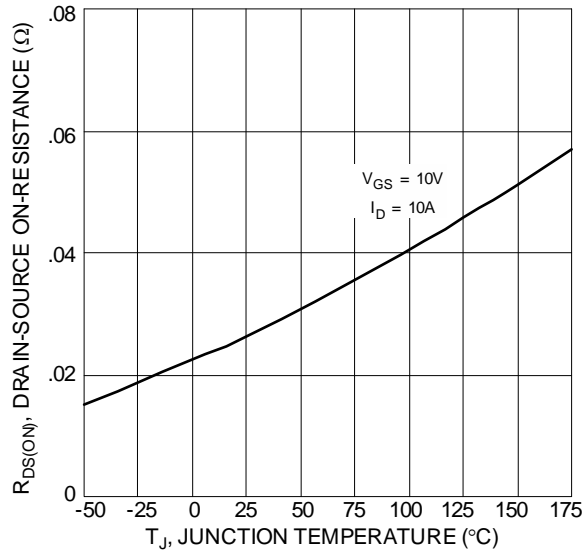
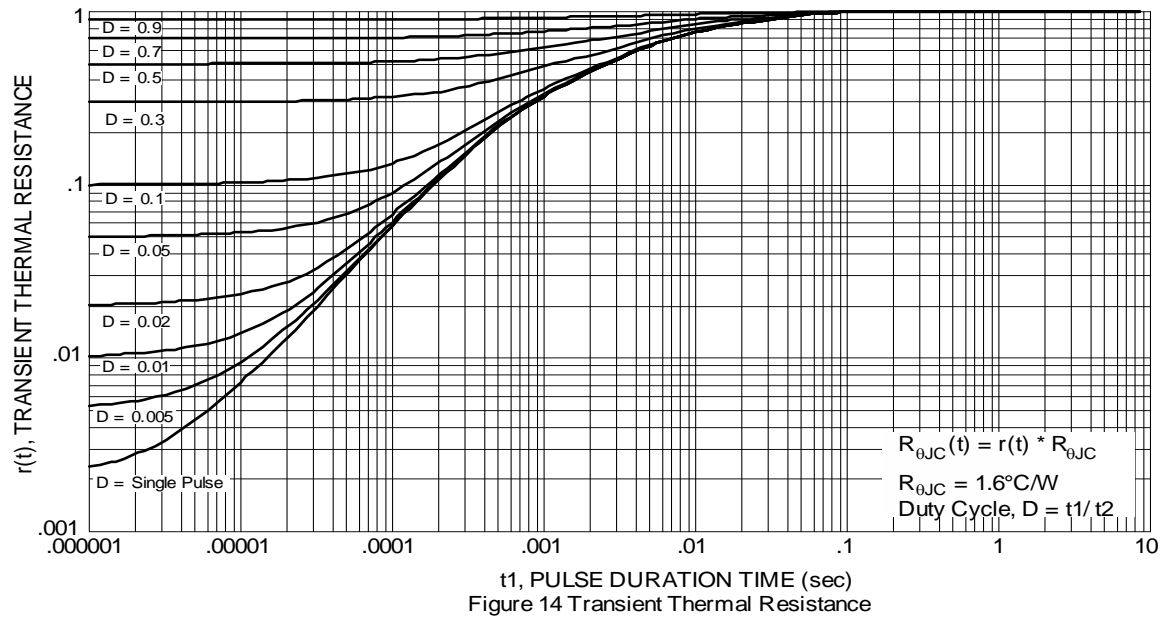
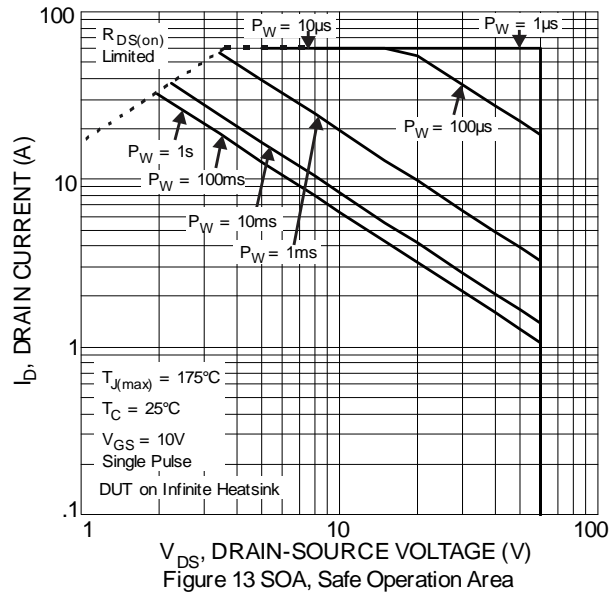


Figure 6 On-Resistance Variation with Temperature

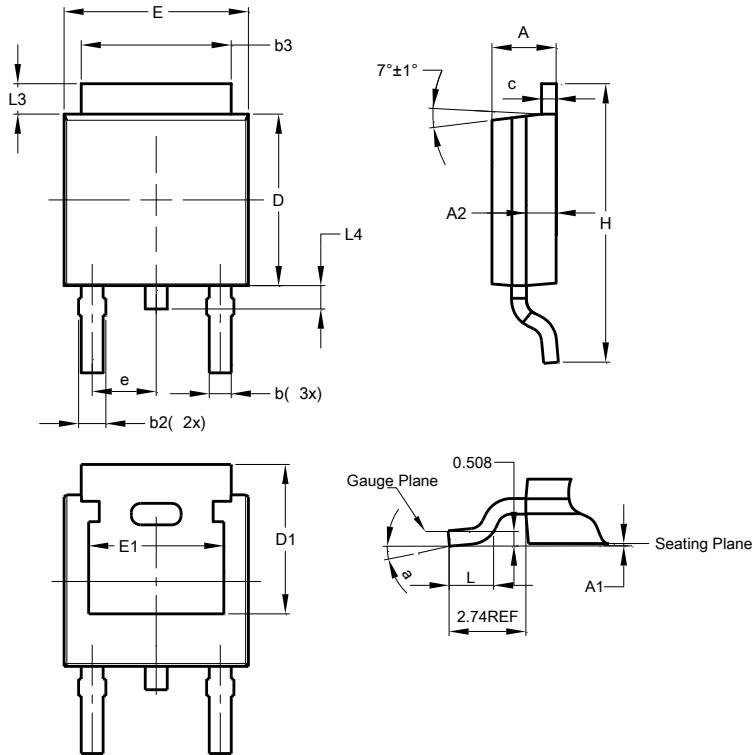




Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

TO252 (DPAK)

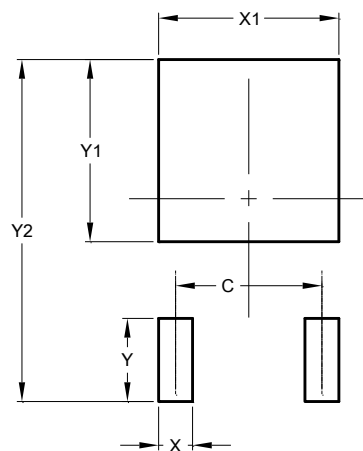


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	—	—
e	—	—	2.286
E	6.45	6.70	6.58
E1	4.32	—	—
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	—
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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